

# NPN/PNP Dual General Purpose Transistor

## BC847BPDV6, SBC847BPDV6

This transistor is designed for general purpose amplifier applications. It is housed in the SOT-563 which is designed for low power surface mount applications.

### Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

### MAXIMUM RATINGS – NPN

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	$V_{CEO}$	45	V
Collector – Base Voltage	$V_{CBO}$	50	V
Emitter – Base Voltage	$V_{EBO}$	6.0	V
Collector Current – Continuous	$I_C$	100	mAdc

### MAXIMUM RATINGS – PNP

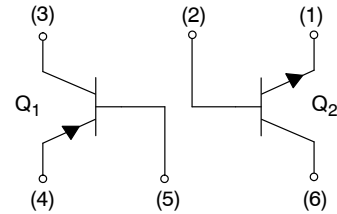
Rating	Symbol	Value	Unit
Collector – Emitter Voltage	$V_{CEO}$	-45	V
Collector – Base Voltage	$V_{CBO}$	-50	V
Emitter – Base Voltage	$V_{EBO}$	-5.0	V
Collector Current – Continuous	$I_C$	-100	mAdc

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

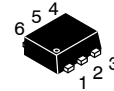
### THERMAL CHARACTERISTICS

Characteristic (One Junction Heated)	Symbol	Max	Unit
Total Device Dissipation (Note 1) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	357 2.9	mW mW/ $^\circ\text{C}$
Thermal Resistance – Junction-to-Ambient (Note 1)	$R_{\theta JA}$	350	$^\circ\text{C}/\text{W}$
Characteristic (Both Junctions Heated)	Symbol	Max	Unit
Total Device Dissipation (Note 1) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	500 4.0	mW mW/ $^\circ\text{C}$
Thermal Resistance – Junction-to-Ambient (Note 1)	$R_{\theta JA}$	250	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

1. FR-4 @ Minimum Pad

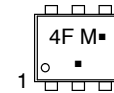


BC847BPDV6T1



SOT-563  
CASE 463A

### MARKING DIAGRAM



- 4F = Specific Device Code
- M = Month Code
- = Pb-Free Package

(Note: Microdot may be in either location)

### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
BC847BPDV6T1G	SOT-563 (Pb-Free)	4 mm pitch 4000/Tape & Reel
SBC847BPDV6T1G	SOT-563 (Pb-Free)	4 mm pitch 4000/Tape & Reel
BC847BPDV6T5G	SOT-563 (Pb-Free)	2 mm pitch 8000/Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

## BC847BPDV6, SBC847BPDV6

### ELECTRICAL CHARACTERISTICS (NPN) ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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#### OFF CHARACTERISTICS

Collector – Emitter Breakdown Voltage ( $I_C = 10\text{ mA}$ )	$V_{(BR)CEO}$	45	–	–	V
Collector – Emitter Breakdown Voltage ( $I_C = 10\ \mu\text{A}$ , $V_{EB} = 0$ )	$V_{(BR)CES}$	50	–	–	V
Collector – Base Breakdown Voltage ( $I_C = 10\ \mu\text{A}$ )	$V_{(BR)CBO}$	50	–	–	V
Emitter – Base Breakdown Voltage ( $I_E = 1.0\ \mu\text{A}$ )	$V_{(BR)EBO}$	6.0	–	–	V
Collector Cutoff Current ( $V_{CB} = 30\text{ V}$ ) ( $V_{CB} = 30\text{ V}$ , $T_A = 150^\circ\text{C}$ )	$I_{CBO}$	–	–	15 5.0	nA $\mu\text{A}$

#### ON CHARACTERISTICS

DC Current Gain ( $I_C = 10\ \mu\text{A}$ , $V_{CE} = 5.0\text{ V}$ ) ( $I_C = 2.0\text{ mA}$ , $V_{CE} = 5.0\text{ V}$ )	$h_{FE}$	– 200	150 290	– 475	–
Collector – Emitter Saturation Voltage ( $I_C = 10\text{ mA}$ , $I_B = 0.5\text{ mA}$ ) ( $I_C = 100\text{ mA}$ , $I_B = 5.0\text{ mA}$ )	$V_{CE(sat)}$	– –	– –	0.25 0.6	V
Base – Emitter Saturation Voltage ( $I_C = 10\text{ mA}$ , $I_B = 0.5\text{ mA}$ ) ( $I_C = 100\text{ mA}$ , $I_B = 5.0\text{ mA}$ )	$V_{BE(sat)}$	– –	0.7 0.9	– –	V
Base – Emitter Voltage ( $I_C = 2.0\text{ mA}$ , $V_{CE} = 5.0\text{ V}$ ) ( $I_C = 10\text{ mA}$ , $V_{CE} = 5.0\text{ V}$ )	$V_{BE(on)}$	580 –	660 –	700 770	mV

#### SMALL-SIGNAL CHARACTERISTICS

Current – Gain – Bandwidth Product ( $I_C = 10\text{ mA}$ , $V_{CE} = 5.0\text{ Vdc}$ , $f = 100\text{ MHz}$ )	$f_T$	100	–	–	MHz
Output Capacitance ( $V_{CB} = 10\text{ V}$ , $f = 1.0\text{ MHz}$ )	$C_{obo}$	–	–	4.5	pF
Noise Figure ( $I_C = 0.2\text{ mA}$ , $V_{CE} = 5.0\text{ Vdc}$ , $R_S = 2.0\text{ k}\Omega$ , $f = 1.0\text{ kHz}$ , $BW = 200\text{ Hz}$ )	NF	–	–	10	dB

## BC847BPDV6, SBC847BPDV6

### ELECTRICAL CHARACTERISTICS (PNP) ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>					
Collector – Emitter Breakdown Voltage ( $I_C = -10\text{ mA}$ )	$V_{(BR)CEO}$	-45	-	-	V
Collector – Emitter Breakdown Voltage ( $I_C = -10\ \mu\text{A}$ , $V_{EB} = 0$ )	$V_{(BR)CES}$	-50	-	-	V
Collector – Base Breakdown Voltage ( $I_C = -10\ \mu\text{A}$ )	$V_{(BR)CBO}$	-50	-	-	V
Emitter – Base Breakdown Voltage ( $I_E = -1.0\ \mu\text{A}$ )	$V_{(BR)EBO}$	-5.0	-	-	V
Collector Cutoff Current ( $V_{CB} = -30\text{ V}$ ) ( $V_{CB} = -30\text{ V}$ , $T_A = 150^\circ\text{C}$ )	$I_{CBO}$	-	-	-15 -4.0	nA $\mu\text{A}$
<b>ON CHARACTERISTICS</b>					
DC Current Gain ( $I_C = -10\ \mu\text{A}$ , $V_{CE} = -5.0\text{ V}$ ) ( $I_C = -2.0\text{ mA}$ , $V_{CE} = -5.0\text{ V}$ )	$h_{FE}$	- 200	150 290	- 475	-
Collector – Emitter Saturation Voltage ( $I_C = -10\text{ mA}$ , $I_B = -0.5\text{ mA}$ ) ( $I_C = -100\text{ mA}$ , $I_B = -5.0\text{ mA}$ )	$V_{CE(sat)}$	- -	- -	-0.3 -0.65	V
Base – Emitter Saturation Voltage ( $I_C = -10\text{ mA}$ , $I_B = -0.5\text{ mA}$ ) ( $I_C = -100\text{ mA}$ , $I_B = -5.0\text{ mA}$ )	$V_{BE(sat)}$	- -	-0.7 -0.9	- -	V
Base – Emitter On Voltage ( $I_C = -2.0\text{ mA}$ , $V_{CE} = -5.0\text{ V}$ ) ( $I_C = -10\text{ mA}$ , $V_{CE} = -5.0\text{ V}$ )	$V_{BE(on)}$	-0.6 -	- -	-0.75 -0.82	V
<b>SMALL – SIGNAL CHARACTERISTICS</b>					
Current – Gain – Bandwidth Product ( $I_C = -10\text{ mA}$ , $V_{CE} = -5.0\text{ Vdc}$ , $f = 100\text{ MHz}$ )	$f_T$	100	-	-	MHz
Output Capacitance ( $V_{CB} = -10\text{ V}$ , $f = 1.0\text{ MHz}$ )	$C_{ob}$	-	-	4.5	pF
Noise Figure ( $I_C = -0.2\text{ mA}$ , $V_{CE} = -5.0\text{ Vdc}$ , $R_S = 2.0\text{ k}\Omega$ , $f = 1.0\text{ kHz}$ , $BW = 200\text{ Hz}$ )	NF	-	-	10	dB

# BC847BPD XV6, SBC847BPD XV6

## TYPICAL NPN CHARACTERISTICS

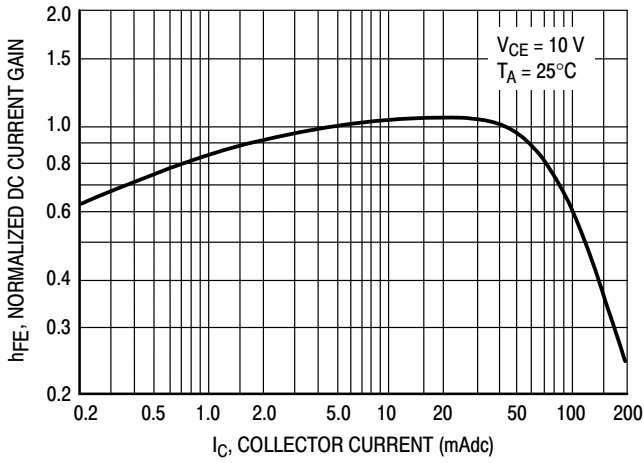


Figure 1. Normalized DC Current Gain

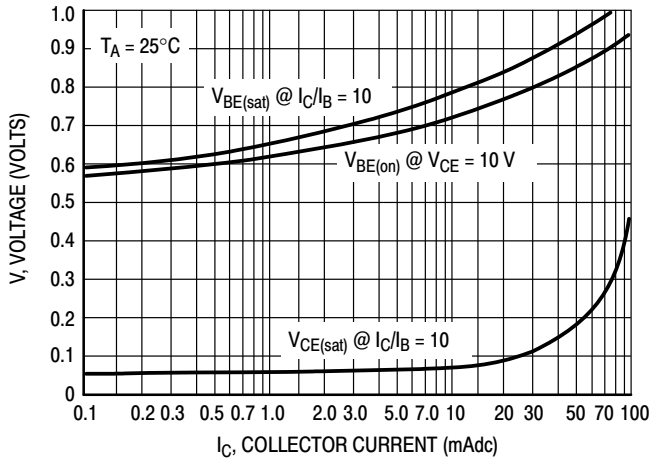


Figure 2. "Saturation" and "On" Voltages

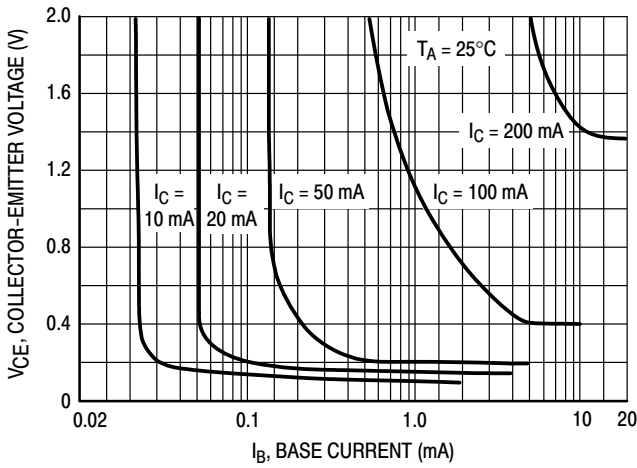


Figure 3. Collector Saturation Region

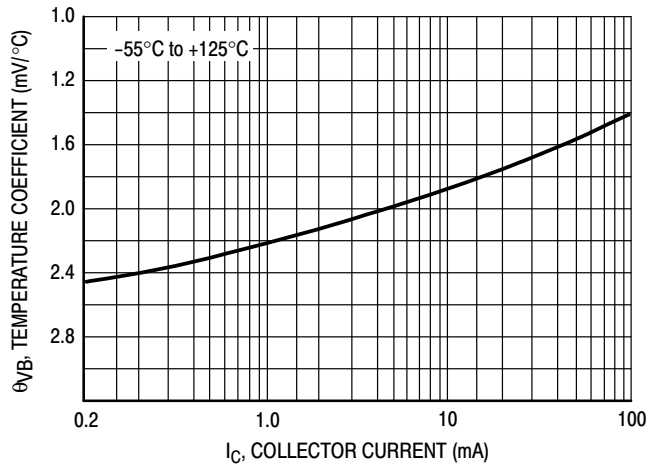


Figure 4. Base-Emitter Temperature Coefficient

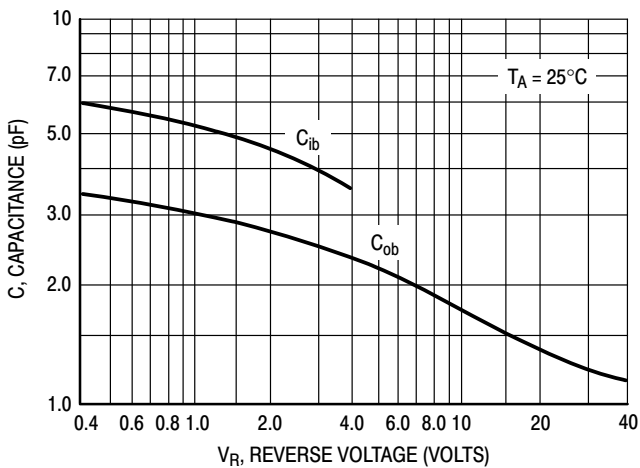


Figure 5. Capacitances

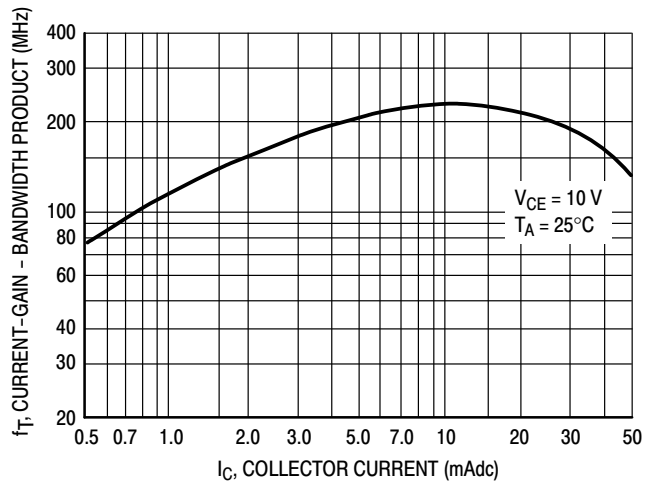


Figure 6. Current-Gain - Bandwidth Product

TYPICAL PNP CHARACTERISTICS

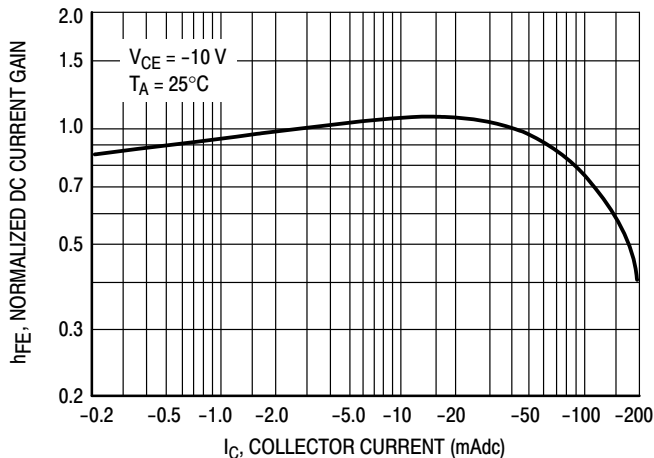


Figure 7. Normalized DC Current Gain

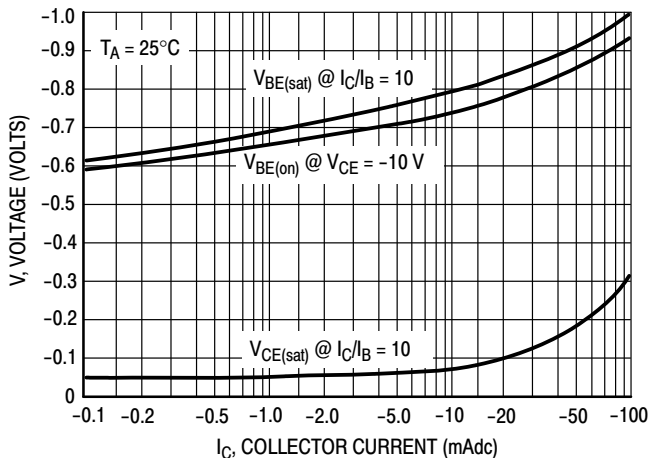


Figure 8. "Saturation" and "On" Voltages

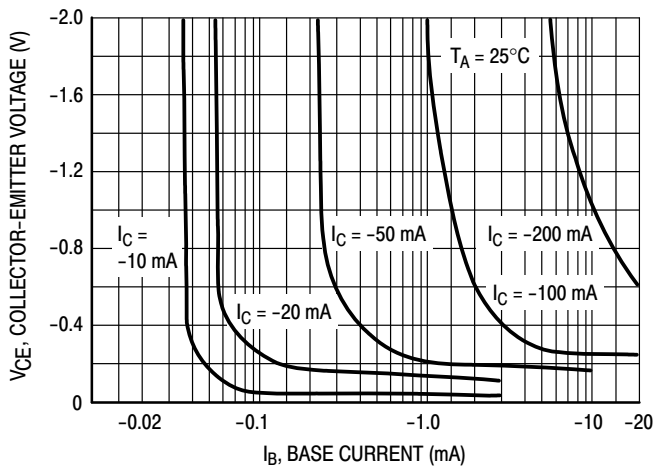


Figure 9. Collector Saturation Region

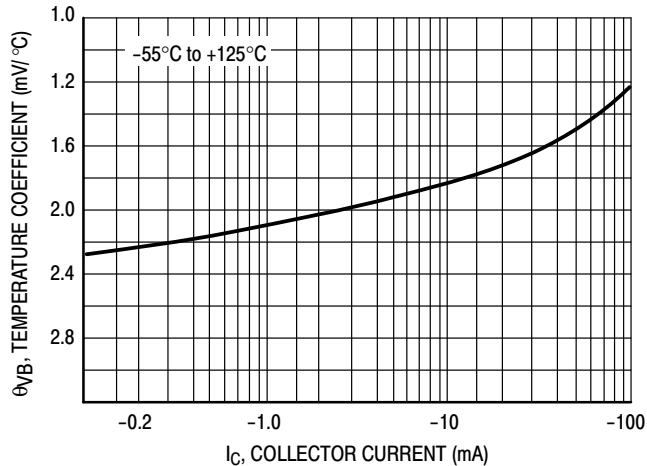


Figure 10. Base-Emitter Temperature Coefficient

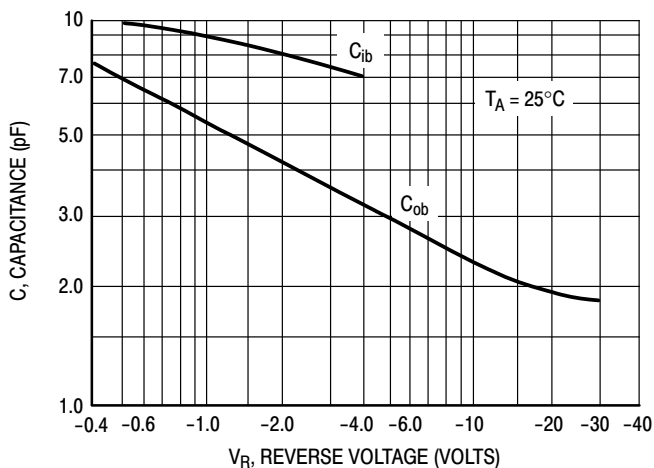


Figure 11. Capacitances

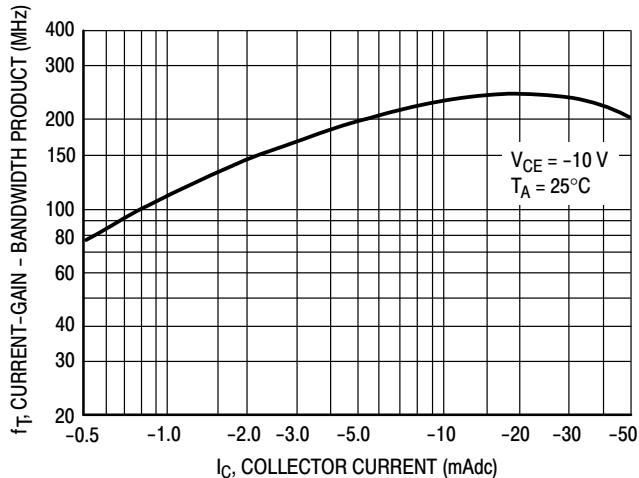
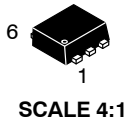


Figure 12. Current-Gain - Bandwidth Product

**MECHANICAL CASE OUTLINE**  
**PACKAGE DIMENSIONS**

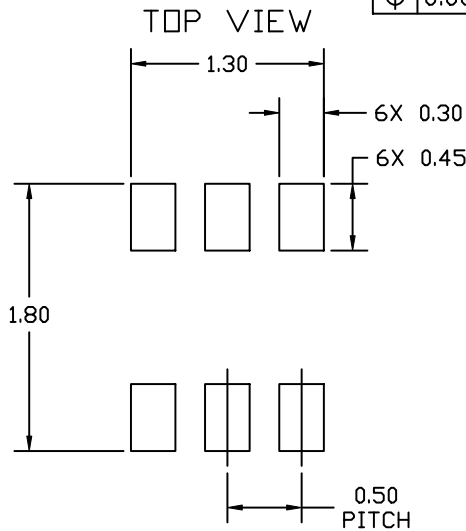
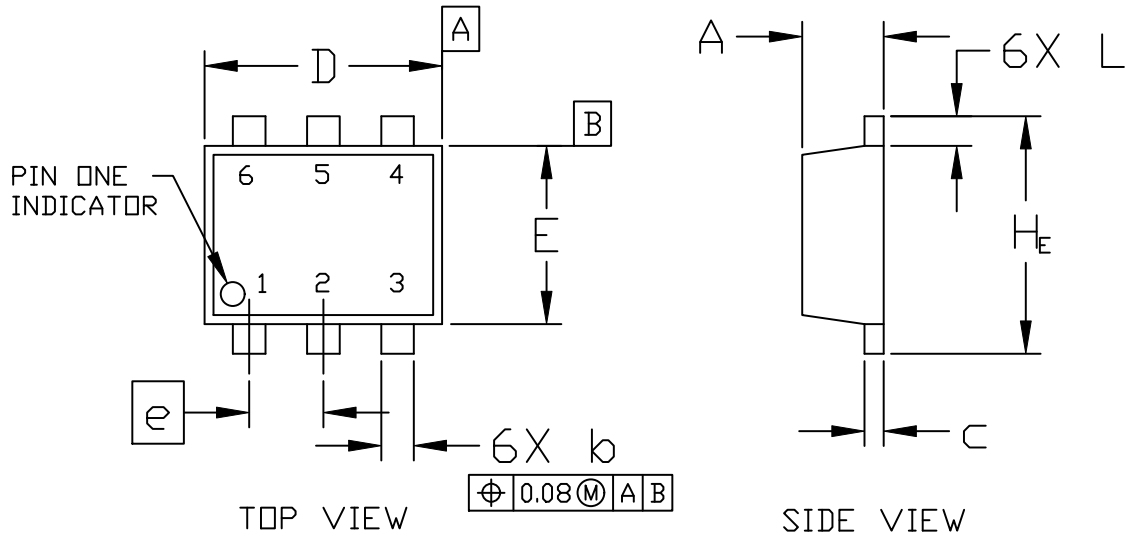


**SOT-563, 6 LEAD**  
CASE 463A  
ISSUE H

DATE 26 JAN 2021

**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.



DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.50	0.55	0.60
b	0.17	0.22	0.27
c	0.08	0.13	0.18
D	1.50	1.60	1.70
E	1.10	1.20	1.30
e	0.50 BSC		
L	0.10	0.20	0.30
H <sub>E</sub>	1.50	1.60	1.70

**RECOMMENDED MOUNTING FOOTPRINT\***

\* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS



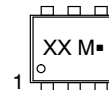
### SOT-563, 6 LEAD

CASE 463A  
ISSUE H

DATE 26 JAN 2021

- |   |  |   |
|---|--|---|
| <p>STYLE 1:<br/>PIN 1. EMITTER 1<br/>2. BASE 1<br/>3. COLLECTOR 2<br/>4. EMITTER 2<br/>5. BASE 2<br/>6. COLLECTOR 1</p> | <p>STYLE 2:<br/>PIN 1. EMITTER 1<br/>2. EMITTER 2<br/>3. BASE 2<br/>4. COLLECTOR 2<br/>5. BASE 1<br/>6. COLLECTOR 1</p>  | <p>STYLE 3:<br/>PIN 1. CATHODE 1<br/>2. CATHODE 1<br/>3. ANODE/ANODE 2<br/>4. CATHODE 2<br/>5. CATHODE 2<br/>6. ANODE/ANODE 1</p> |
| <p>STYLE 4:<br/>PIN 1. COLLECTOR<br/>2. COLLECTOR<br/>3. BASE<br/>4. EMITTER<br/>5. COLLECTOR<br/>6. COLLECTOR</p>      | <p>STYLE 5:<br/>PIN 1. CATHODE<br/>2. CATHODE<br/>3. ANODE<br/>4. ANODE<br/>5. CATHODE<br/>6. CATHODE</p>                | <p>STYLE 6:<br/>PIN 1. CATHODE<br/>2. ANODE<br/>3. CATHODE<br/>4. CATHODE<br/>5. CATHODE<br/>6. CATHODE</p>                       |
| <p>STYLE 7:<br/>PIN 1. CATHODE<br/>2. ANODE<br/>3. CATHODE<br/>4. CATHODE<br/>5. ANODE<br/>6. CATHODE</p>               | <p>STYLE 8:<br/>PIN 1. DRAIN<br/>2. DRAIN<br/>3. GATE<br/>4. SOURCE<br/>5. DRAIN<br/>6. DRAIN</p>                        | <p>STYLE 9:<br/>PIN 1. SOURCE 1<br/>2. GATE 1<br/>3. DRAIN 2<br/>4. SOURCE 2<br/>5. GATE 2<br/>6. DRAIN 1</p>                     |
| <p>STYLE 10:<br/>PIN 1. CATHODE 1<br/>2. N/C<br/>3. CATHODE 2<br/>4. ANODE 2<br/>5. N/C<br/>6. ANODE 1</p>              | <p>STYLE 11:<br/>PIN 1. EMITTER 2<br/>2. BASE 2<br/>3. COLLECTOR 1<br/>4. EMITTER 1<br/>5. BASE 1<br/>6. COLLECTOR 2</p> |   |

### GENERIC MARKING DIAGRAM\*



XX = Specific Device Code  
M = Month Code  
▪ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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